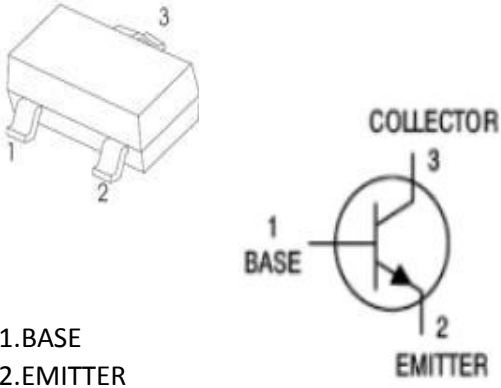


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors																																										
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p style="text-align: center;">Marking :2D</p>	<p style="text-align: center;">Features</p> <p style="text-align: center;">※ High Breakdown Voltage</p>																																										
<p><b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b></p>																																											
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="text-align: center;">Parameter</th> <th style="text-align: center;">Symbol</th> <th style="text-align: center;">Value</th> <th style="text-align: center;">Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td>VCBO</td> <td>-300</td> <td>V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td>VCEO</td> <td>-300</td> <td>V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td>VEBO</td> <td>-5</td> <td>V</td> </tr> <tr> <td>Collector Current -Continuous</td> <td>IC</td> <td>-200</td> <td>mA</td> </tr> <tr> <td>Collector Current -Pulsed</td> <td>ICM</td> <td>-500</td> <td>mA</td> </tr> <tr> <td>Collector Power Dissipation</td> <td>PC</td> <td>300</td> <td>mW</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td>ROJA</td> <td>417</td> <td>°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td>Tj</td> <td>150</td> <td>°C</td> </tr> <tr> <td>Storage Temperature</td> <td>Tstg</td> <td>-55~+150</td> <td>°C</td> </tr> </tbody> </table>	Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	-300	V	Collector-Emitter Voltage	VCEO	-300	V	Emitter-Base Voltage	VEBO	-5	V	Collector Current -Continuous	IC	-200	mA	Collector Current -Pulsed	ICM	-500	mA	Collector Power Dissipation	PC	300	mW	Thermal Resistance From Junction To Ambient	ROJA	417	°C/W	Junction Temperature	Tj	150	°C	Storage Temperature	Tstg	-55~+150	°C			
Parameter	Symbol	Value	Unit																																								
Collector-Base Voltage	VCBO	-300	V																																								
Collector-Emitter Voltage	VCEO	-300	V																																								
Emitter-Base Voltage	VEBO	-5	V																																								
Collector Current -Continuous	IC	-200	mA																																								
Collector Current -Pulsed	ICM	-500	mA																																								
Collector Power Dissipation	PC	300	mW																																								
Thermal Resistance From Junction To Ambient	ROJA	417	°C/W																																								
Junction Temperature	Tj	150	°C																																								
Storage Temperature	Tstg	-55~+150	°C																																								

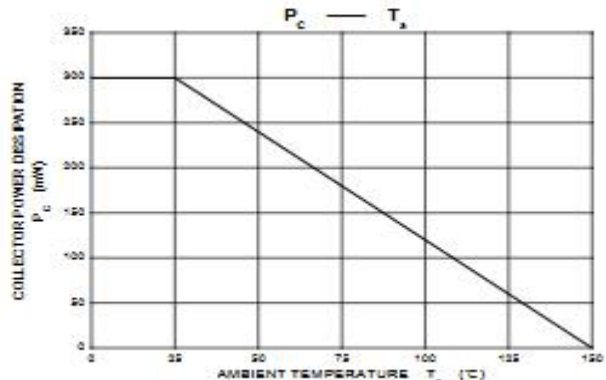
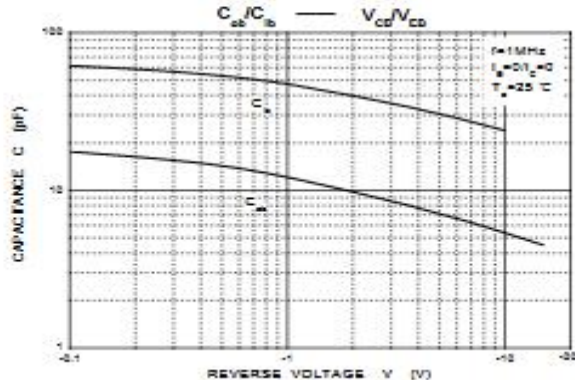
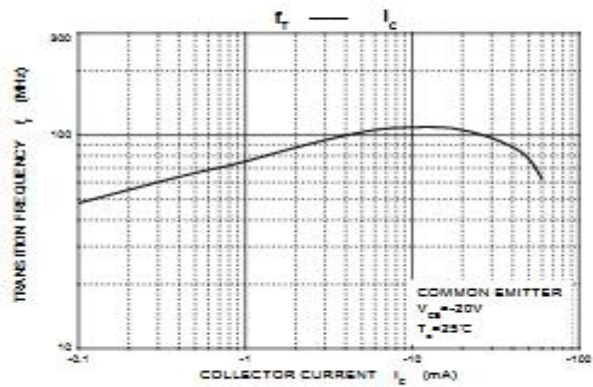
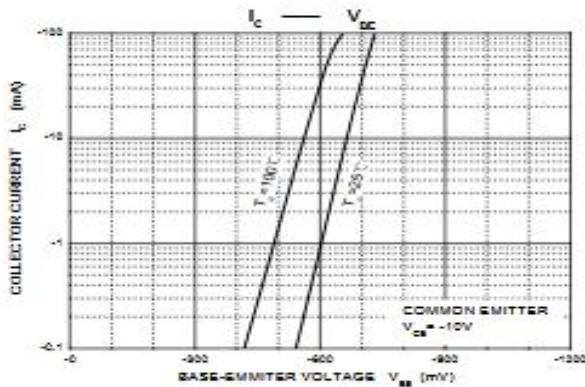
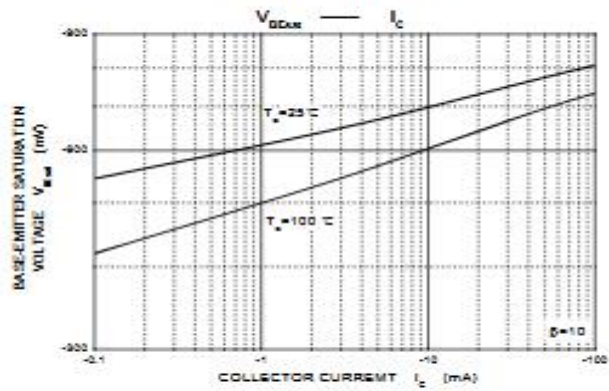
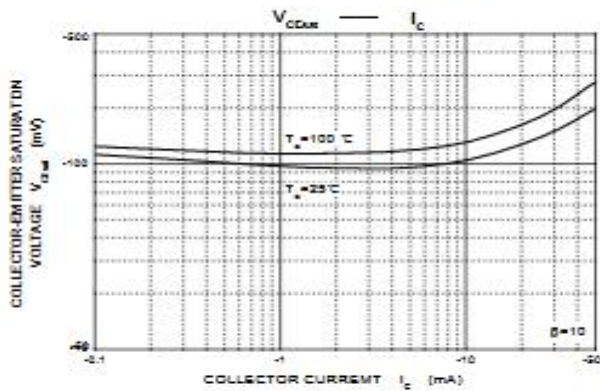
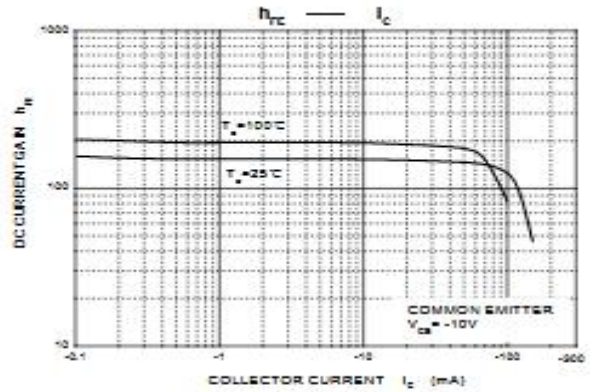
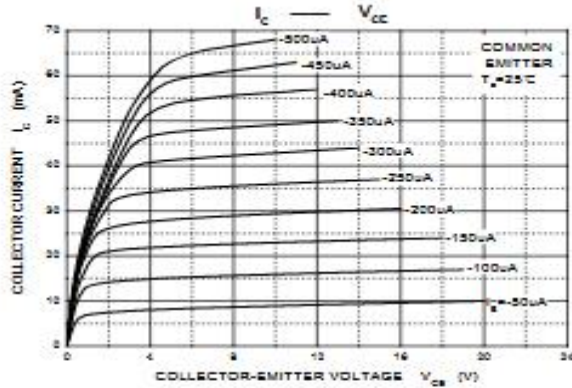
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100µA, IE=0	-150	365	-800	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-150	310	-800	V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100µA, IC=0	-5	11	-30	V
Collector cut-off current	ICBO	VCB=-120 V , IE=0			-0.25	µA
Collector cut-off current	ICEO	VCB=-150V , IE=0			-5	µA
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.1	µA
DC current gain	hFE	VCE=-5V, IC= -1mA	80			
	hFE	VCE=-5V, IC= -10mA	100		200	
	hFE	VCE=-5V, IC= -50mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC=-50 mA, IB= -5mA			-2	V
Base-emitter saturation voltage	VBE(sat)	IC=-50 mA, IB=- 5mA			-1	V
Transition frequency	fT	VCE=-20V, IC= -10mA f=300MHz	50			MHz

**CLASSIFICATION OF hFI**

Rank	L	H	J
Range	80-100	100-200	200-250

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)